BUK663R5-55C

N-channel TrenchMOS FET

Rev. 01 — 3 August 2010 **Objective data sheet**

1. Product profile

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for intermediate level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V Automotive systems
- ABS/ESP
- Engine management
- HVAC
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. Quick reference data

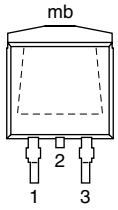
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	-	55	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see Figure 1	[1]	-	-	100	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2		-	-	263	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 15 A; T_j = 25 °C; see Figure 5		-	2.7	3.5	mΩ
Avalanche ruggedness							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 100 A; $V_{sup} \leq 55$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	551	mJ

[1] Continuous current is limited by package.

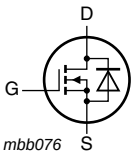
2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	Drain		
3	S	source		
mb	D	mounting base; connected to drain		



SOT404 (D2PAK)



3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK663R5-55C	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

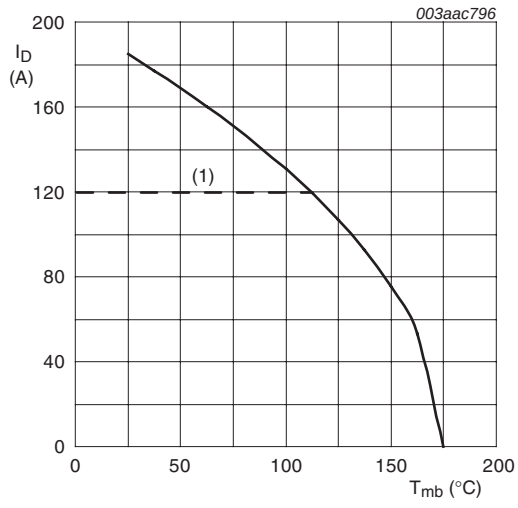
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	55	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see Figure 1	[1]	-	100	A
		T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 1	[1]	-	100	A
I_{DM}	peak drain current	T_{mb} = 25 °C; $t_p \leq 10$ µs; pulsed		-	757	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2		-	263	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C	[1]	-	100	A
I_{SM}	peak source current	$t_p \leq 10$ µs; pulsed; T_{mb} = 25 °C		-	757	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 100 A; $V_{sup} \leq 55$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	551	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy		[2][3][4]	-	-	J

[1] Continuous current is limited by package.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

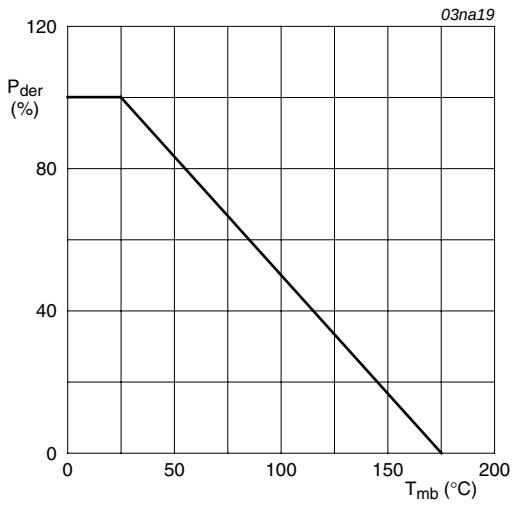
[4] Refer to application note AN10273 for further information.



$V_{GS} \geq 10\,V$

(1) Capped at 100 A due to package.

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see Figure 3	-	-	0.57	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

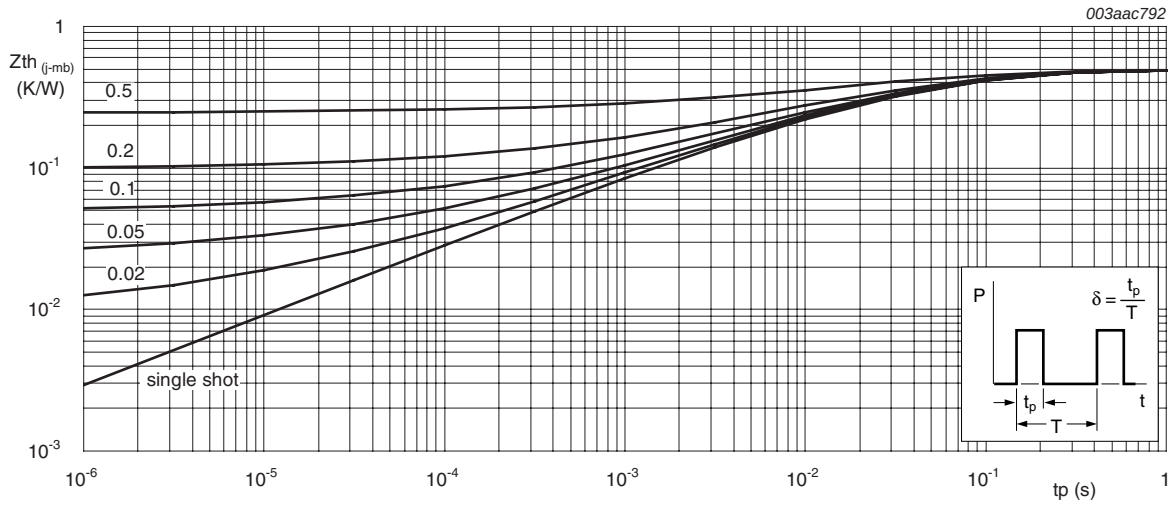
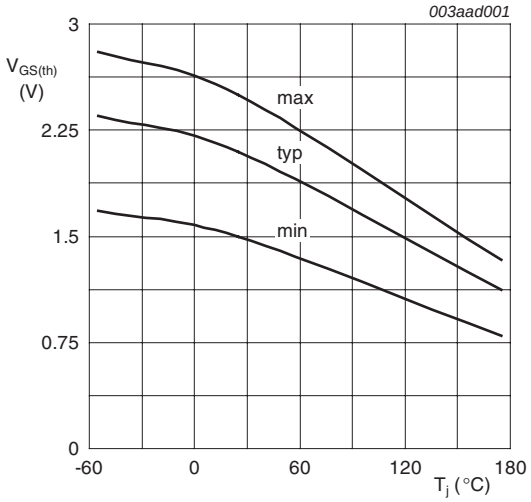


Fig 3. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

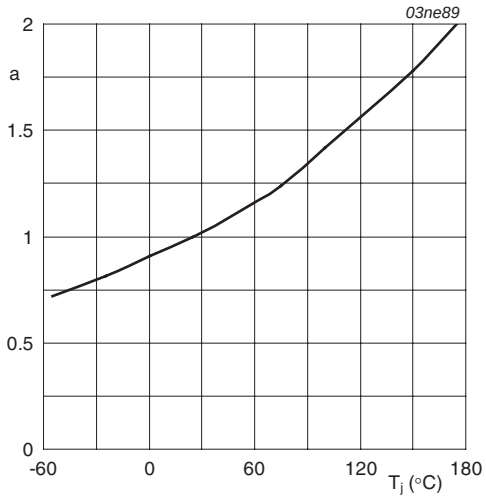
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	55	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 4	1.5	2.1	2.5	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; see Figure 4	-	-	2.8	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; see Figure 4	0.8	-	-	V
I_{DSS}	drain leakage current	V_{DS} = 55 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	µA
		V_{DS} = 55 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	µA
I_{GSS}	gate leakage current	V_{DS} = 0 V; V_{GS} = 20 V; T_j = 25 °C	-	2	100	nA
		V_{DS} = 0 V; V_{GS} = -20 V; T_j = 25 °C	-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 15 A; T_j = 25 °C; see Figure 5	-	[tbd]	[tbd]	mΩ
		V_{GS} = 10 V; I_D = 15 A; T_j = 25 °C; see Figure 5	-	2.7	3.5	mΩ
		V_{GS} = 4.5 V; I_D = 15 A; T_j = 25 °C; see Figure 5	-	[tbd]	[tbd]	mΩ
		V_{GS} = 10 V; I_D = 15 A; T_j = 175 °C; see Figure 5	-	-	7.4	mΩ
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 40 V; V_{GS} = 10 V	-	[tbd]	[tbd]	nC
		I_D = 25 A; V_{DS} = 40 V; V_{GS} = 5 V	-	[tbd]	[tbd]	nC
Q_{GS}	gate-source charge	I_D = 25 A; V_{DS} = 40 V; V_{GS} = 10 V	-	[tbd]	[tbd]	nC
Q_{GD}	gate-drain charge		-	[tbd]	[tbd]	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C	-	[tbd]	[tbd]	pF
C_{oss}	output capacitance		-	[tbd]	[tbd]	pF
C_{rss}	reverse transfer capacitance		-	[tbd]	[tbd]	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω	-	[tbd]	[tbd]	ns
t_r	rise time		-	[tbd]	[tbd]	ns
$t_{d(off)}$	turn-off delay time		-	[tbd]	[tbd]	ns
t_f	fall time		-	[tbd]	[tbd]	ns
L_D	internal drain inductance	from drain lead 6 mm from package to centre of die ; T_j = 25 °C	-	4.5	-	nH
L_S	internal source inductance	from source lead to source bond pad ; T_j = 25 °C	-	7.5	-	nH
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C	-	0.85	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 25 V	-	[tbd]	[tbd]	ns
Q_r	recovered charge		-	[tbd]	[tbd]	nC



$$I_D = 1mA; V_{DS} = V_{GS}$$

Fig 4. Gate-source threshold voltage as a function of junction temperature

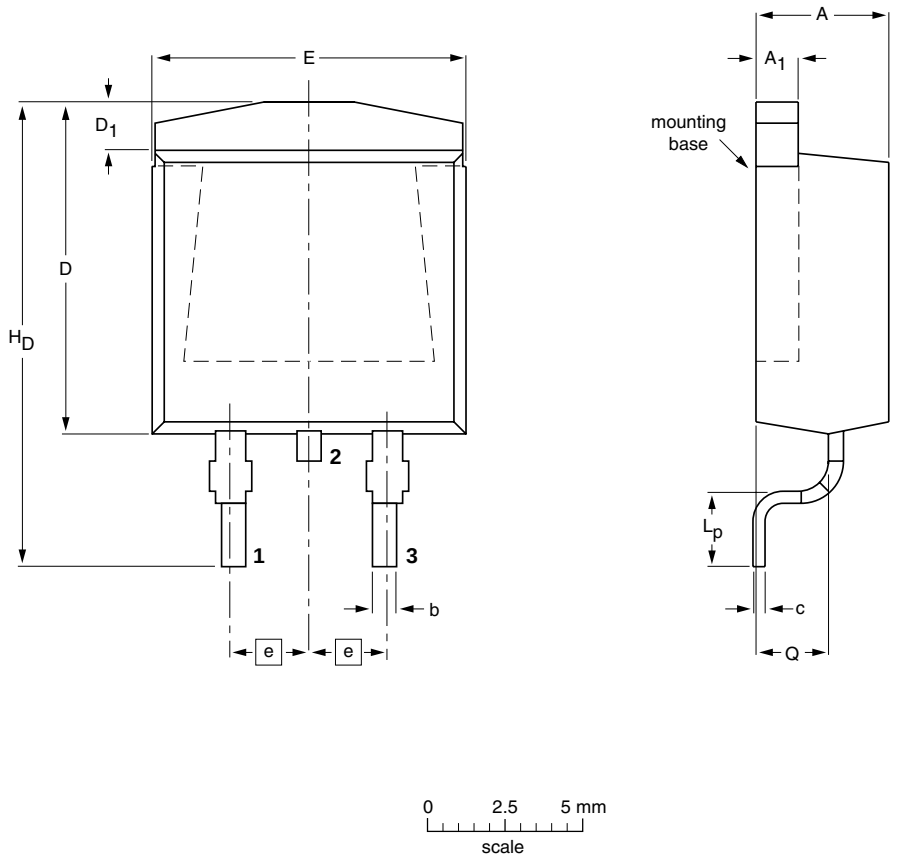


$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 5. Normalized drain-source on-state resistance factor as a function of junction temperature

7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) **SOT404**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	c	D max.	D_1	E	e	L_p	H_D	Q
mm	4.50 4.10	1.40 1.27	0.85 0.60	0.64 0.46	11	1.60 1.20	10.30 9.70	2.54	2.90 2.10	15.80 14.80	2.60 2.20

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT404						~~05-02-11~~ 06-03-16

Fig 6. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK663R5-55C v.1	20100803	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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